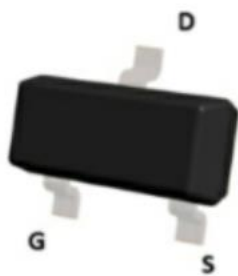


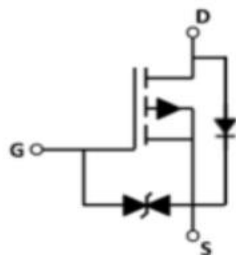
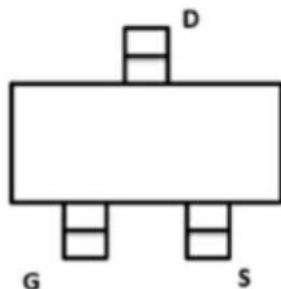
YJL3415A

P-Channel Enhancement Mode Field Effect Transistor



Top View

SOT-23



Product Summary

- V_{DS} -20V
- I_D -5.6A
- $R_{DS(ON)}$ (at $V_{GS}=-4.5V$) <36 mohm
- $R_{DS(ON)}$ (at $V_{GS}=-2.5V$) <49 mohm
- $R_{DS(ON)}$ (at $V_{GS}=-1.8V$) <69 mohm
- ESD Protected Up to 2.5KV (HBM)

General Description

- Trench Power LV MOSFET technology
- High Density Cell Design for Low $R_{DS(ON)}$
- High Speed switching

Applications

- Battery protection
- Load switch
- Power management

■ Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Maximum	Unit
Drain-source Voltage	V_{DS}	-20	V
Gate-source Voltage	V_{GS}	± 12	V
Drain Current	I_D	$T_A=25^\circ C$ Steady State	-5.6
		$T_A=70^\circ C$ Steady State	-4.5
Pulsed Drain Current ^A	I_{DM}	-23	A
Total Power Dissipation @ $T_A=25^\circ C$ Steady State	P_D	1.3	W
Thermal Resistance Junction-to-Ambient @ Steady State ^B	$R_{\theta JA}$	96	$^\circ C/W$
Junction and Storage Temperature Range	T_J, T_{STG}	-55~+150	$^\circ C$

■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJL3415A	F2	3415.	3000	30000	120000	7" reel

YJL3415A

■ Electrical Characteristics (T_J=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =-250μA	-20			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-20V, V _{GS} =0V, T _C =25°C			-1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} = ±12V, V _{DS} =0V		3	±15	μA
		V _{GS} = ±10V, V _{DS} =0V		1	±5	μA
		V _{GS} = ±5V, V _{DS} =0V		50	±200	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250μA	-0.35	-0.57	-0.9	V
Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} = -4.5V, I _D =-5.6A		29	36	mΩ
		V _{GS} = -2.5V, I _D =-4A		36	49	
		V _{GS} = -1.8V, I _D =-3A		49	69	
Diode Forward Voltage	V _{SD}	I _S =-5.6A, V _{GS} =0V		-0.8	-1.2	V
Maximum Body-Diode Continuous Current	I _S				-5.6	A
Dynamic Parameters						
Input Capacitance	C _{iss}	V _{DS} =-10V, V _{GS} =0V, f=1MHZ		698		pF
Output Capacitance	C _{oss}			120		
Reverse Transfer Capacitance	C _{rss}			79		
Switching Parameters						
Total Gate Charge	Q _g	V _{GS} =-4.5V, V _{DD} =-10V, I _D =-4A		7.2		nC
Gate Source Charge	Q _{gs}			1.2		
Gate Drain Charge	Q _{gd}			1.6		
Turn-on Delay Time	t _{D(on)}	V _{GS} =-4.5V, V _{DD} =-10V, R _L =2.5Ω, R _{GEN} =3Ω		15		ns
Turn-on Rise Time	t _r			63		
Turn-off Delay Time	t _{D(off)}			21		
Turn-off Fall Time	t _f			12		

A. Pulse Test: Pulse Width ≤ 300us, Duty cycle ≤ 2%.

B. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch.

■ Typical Performance Characteristics

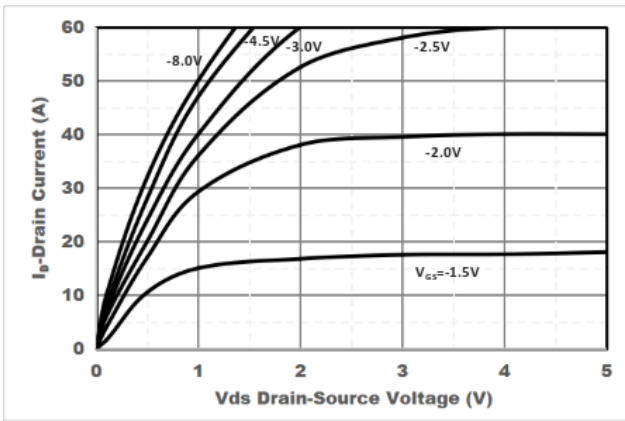


Figure1. Output Characteristics

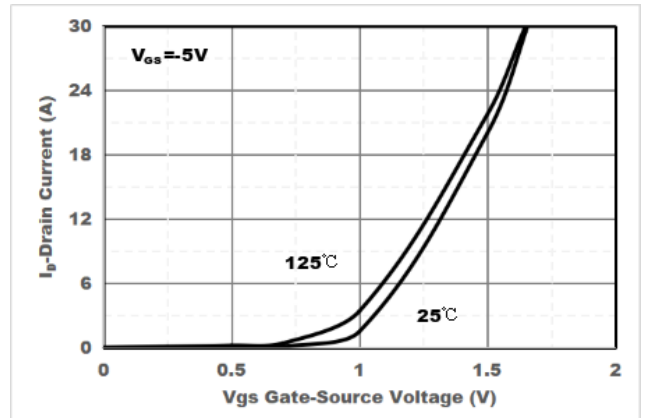


Figure2. Transfer Characteristics

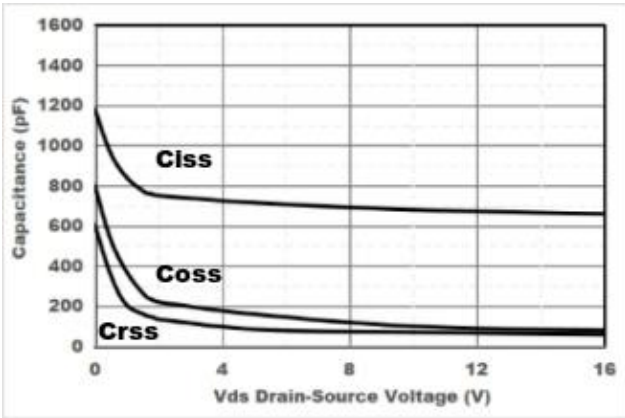


Figure3. Capacitance Characteristics

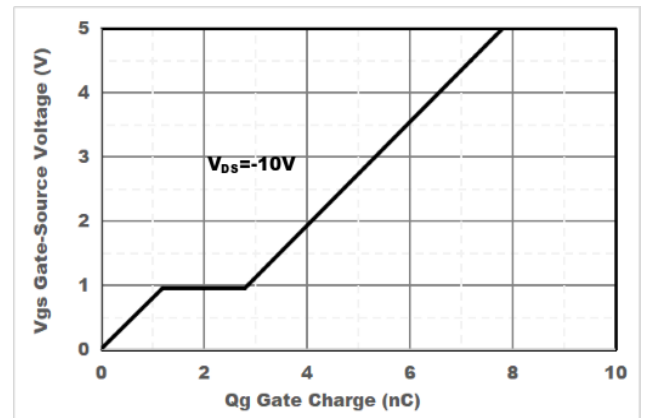


Figure4. Gate Charge

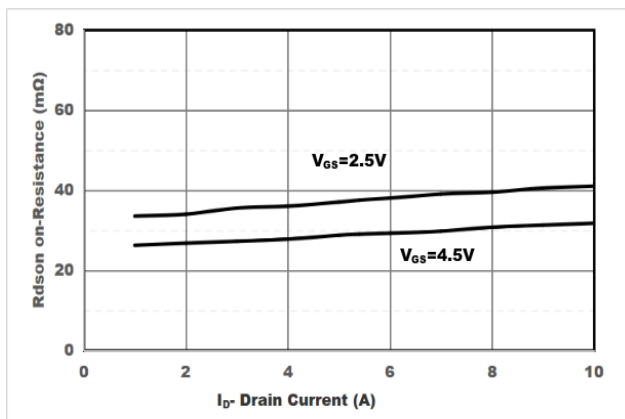


Figure5. Drain-Source on Resistance

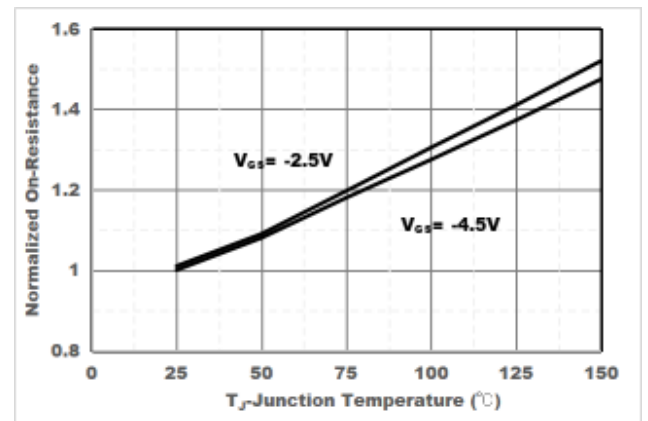
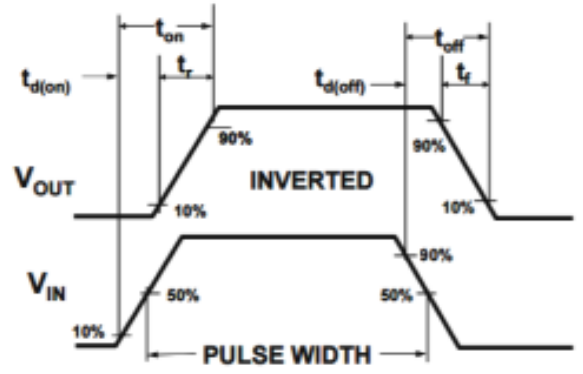
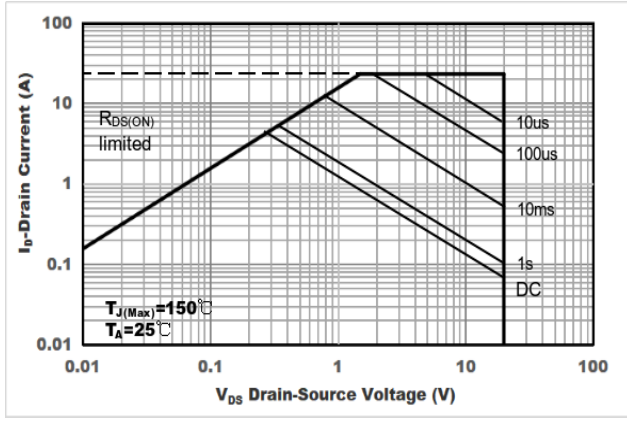


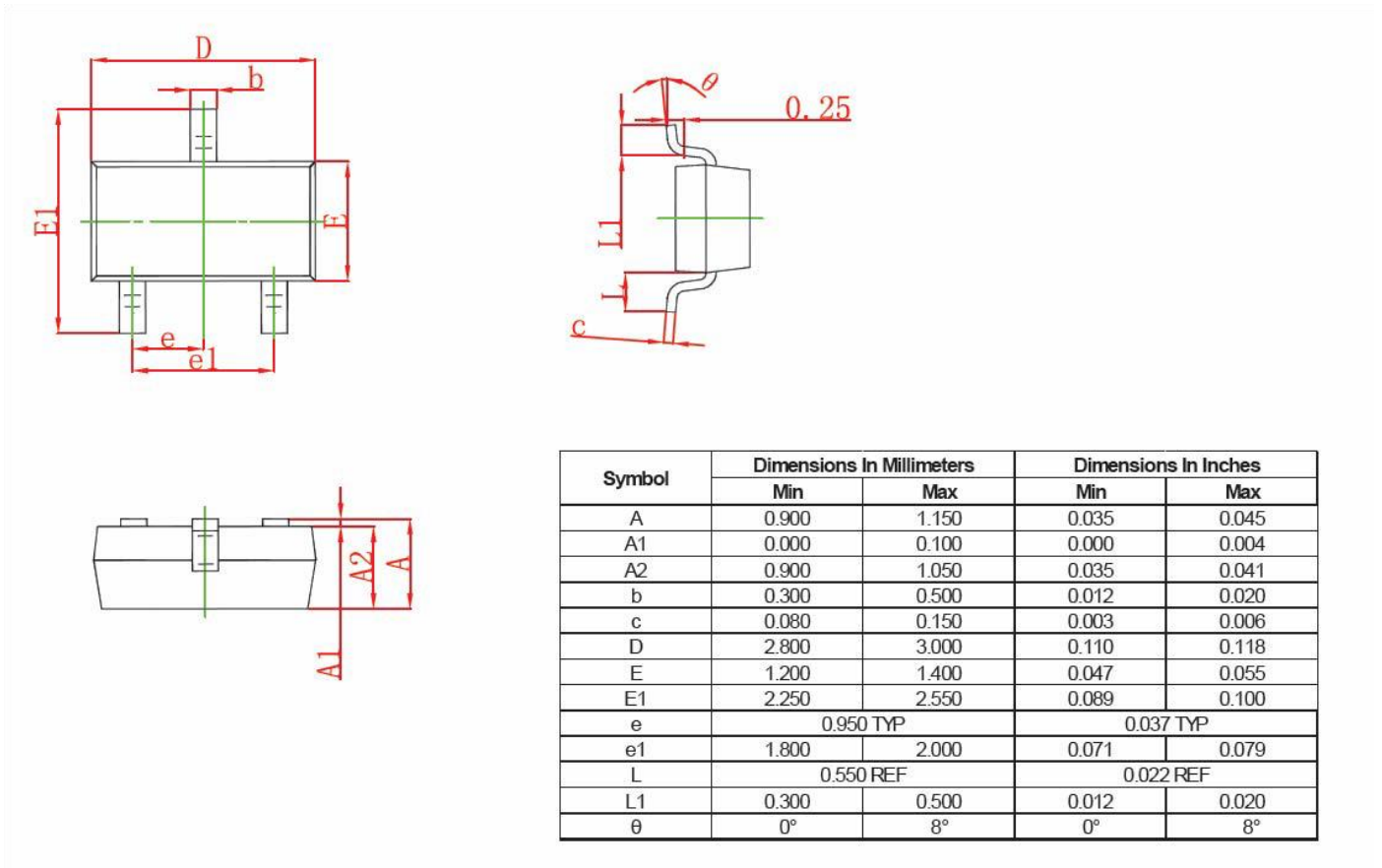
Figure6. Drain-Source on Resistance

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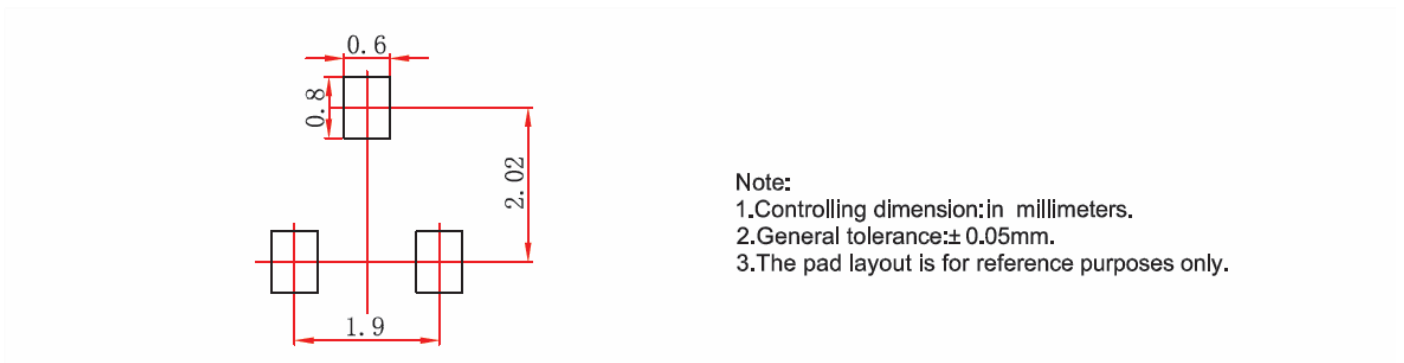


YJL3415A

■ SOT-23 Package information



■ SOT-23 Suggested Pad Layout



YJL3415A

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